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TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

		Application Number	10/514,429
		Filing Date	July 12, 2005
		First Named Inventor	Robert DWILINSKI
		Art Unit	2879
		Examiner Name	Not Yet Assigned
Total Number of Pages in This Submission	4	Attorney Docket Number	204552033800

ENCLOSURES (Check all that apply)

<input type="checkbox"/> Fee Transmittal Form	<input type="checkbox"/> Drawing(s)	<input type="checkbox"/> After Allowance Communication to TC
<input type="checkbox"/> Fee Attached	<input type="checkbox"/> Licensing-related Papers	<input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences
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Remarks		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm Name	MORRISON & FOERSTER LLP		
Signature			
Printed name	Raj S. Dave		
Date	December 19, 2005	Reg. No.	42,465



PATENT
Docket No. 204552033800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Robert DWILINSKI et al.

Serial No.: 10/514,429

Filing Date: July 12, 2005

For: PHOSPHOR SINGLE CRYSTAL
SUBSTRATE AND METHOD FOR
PREPARING THE SAME, AND
NITRIDE SEMICONDUCTOR DEVICE
USING THE SAME

Examiner: Not Yet Assigned

Group Art Unit: 2879

**SUPPLEMENTAL INFORMATION DISCLOSURE
STATEMENT UNDER 37 C.F.R. § 1.97 & 1.98**

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. § 1.97 and § 1.98, Applicants submit for consideration in the above-identified application the documents listed on the attached Form PTO/SB/08a/b. Copies of the non-patent literature are also submitted herewith. The Examiner is requested to make these documents of record.

Six of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 13-18) were cited in a Notification mailed September 27, 2005, directed to a related foreign application JP2003-503864, and have not been previously cited; one of the documents listed on the attached Form PTO/SB/08a/b (Cite No. 12) was cited in an Office Action mailed October 19, 2005, directed to a related application US 10/147,319, and has not been previously cited; two of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 1 and 2) were cited in an Office Action mailed October 4, 2005, directed to a related application US 10/479,858, and have not been previously cited; and nine of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 3-11) were cited in an Office Action mailed November 4, 2005, directed to a related

application US 10/493,747, and have not been previously cited. A certification under 37 C.F.R. § 1.97(e)(1) follows:

I hereby certify that each item of information was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

This Information Disclosure Statement is submitted within three months of the application filing date or before mailing of a first Office Action on the merits; accordingly, no fee or separate requirements are required.

Applicants would appreciate the Examiner initialing and returning the Form PTO/SB/08a/b, indicating that the information has been considered and made of record herein.

The information contained in this Supplemental Information Disclosure Statement under 37 C.F.R. § 1.97 and § 1.98 is not to be construed as a representation that: (i) a complete search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

In the unlikely event that the transmittal form is separated from this document and the Patent Office determines that an extension and/or other relief (such as payment of a fee under 37 C.F.R. § 1.17 (p)) is required, Applicants petitions for any required relief including extensions of time and authorize the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952** referencing **204552033800**.

Dated: December 19, 2005

Respectfully submitted,

By

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Substitute for form 1449/PTO				Complete if Known	
				Application Number	10/514,429
				Filing Date	July 12, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	2879
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	204552033800

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
1.	5,096,860-A	03-17-1992	NADKARNI		
2.	5,589,153-A	12-31-1996	GARCES		
3.	6,252,261-B1	06-26-2001	USUI		
4.	6,468,882-B2	10-22-2002	MOTOKI		
5.	6,509,651-B1	01-21-2003	MATSUBARA		
6.	6,720,586-B1	04-13-2004	KIDOGUCHI		
7.	2002/0014631-A1	02-07-2002	IWATA		
8.	2002/0031153-A1	03-14-2002	NIWA		
9.	2002/0047113-A1	04-25-2002	OHNO		
10.	2002/0063258-A1	05-30-2002	MOTOKI		
11.	2002/0078881-A1	06-27-2002	CUOMO		
12.	2004/0139912-A1	07-22-2004	TOMASZ DWILINSKI		

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
					T ⁶

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
	13.	Akasaki, I. et al. (1991). "Growth and Properties of Single Crystalline GaN Films by Hydride Vapor Phase Epitaxy," <i>Crystal Properties and Preparation</i> 32-34:154-157.			
	14.	Chu, T. L. et al. (1974). "Crystal Growth and Characterization of Gallium Nitride," <i>J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY</i> 121-1:159-162.			
	15.	Kaschner, A. et al. (1999). "Influence of Doping on the Lattice Dynamics of Gallium Nitride," <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G3.57.			
	16.	Kim, S. T. et al. (1998). "Preparation and Properties of Free-standing HVPE Grown GaN Substrates," <i>Journal of Crystal Growth</i> 194:37-42.			
	17.	Kuroda, Naotaka et al. (1998). "Precise Control of Pn-junction Profiles for GaN-based LD structures Using GaN Substrates with Low Dislocation Densities," <i>Journal of Crystal Growth</i> 189/190:551-555.			
	18.	Motoki, Kensaku et al. (2001). "Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a Starting Substrate," <i>J. Appl. Phys.</i> 40:L140-L143.			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Date Considered
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